



P-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	-60 V
I_D	-0.26 A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	3
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	3.5
Gate-Source ESD Rating Up to 2KV (HBM)	





Typical Electrical and Thermal Characteristics Diagrams

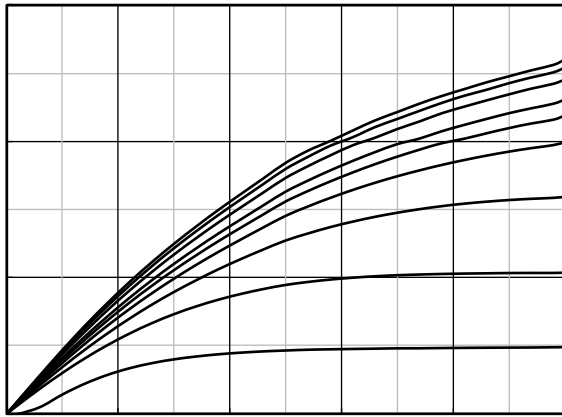


Figure 1. Output Characteristics

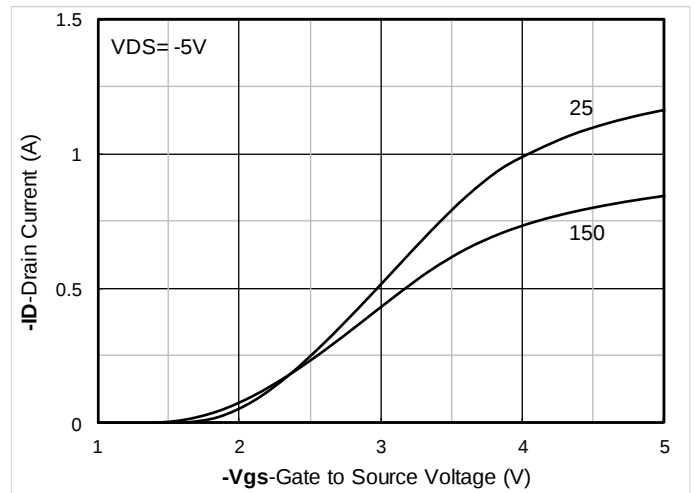


Figure 2. Transfer Characteristics

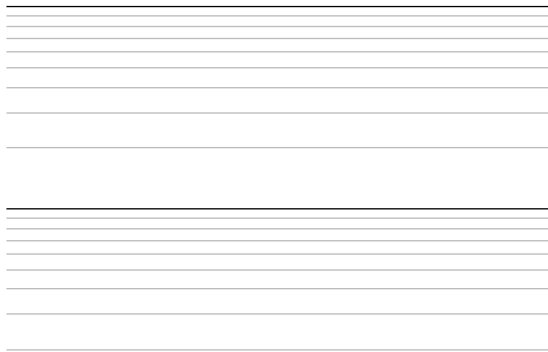


Figure 3. Capacitance Characteristics

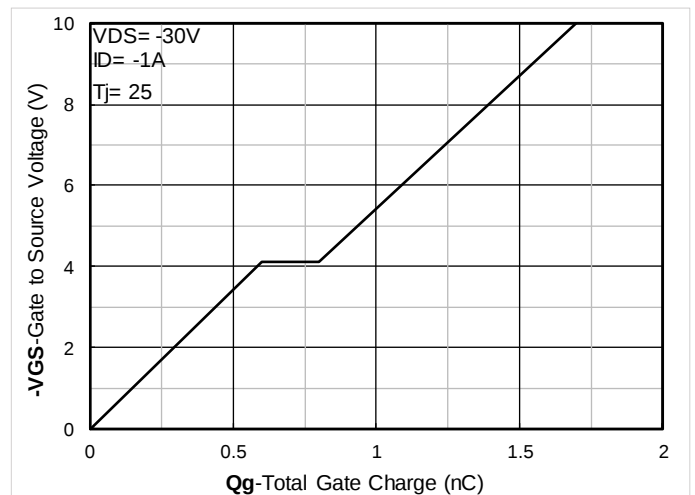


Figure 4. Gate Charge

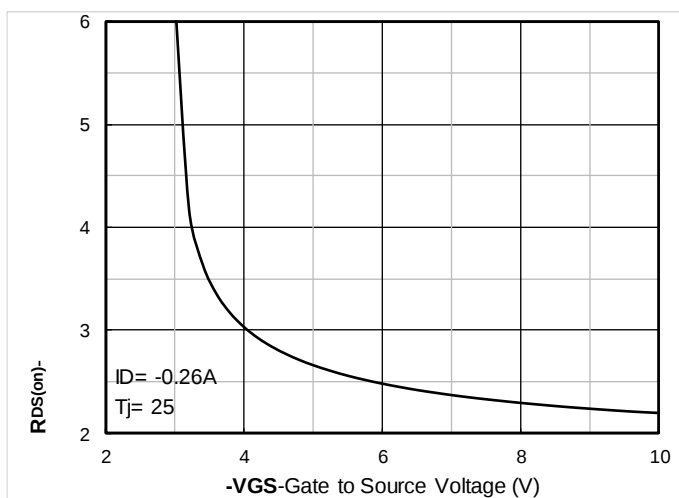


Figure 5. On-Resistance vs Gate to Source Voltage

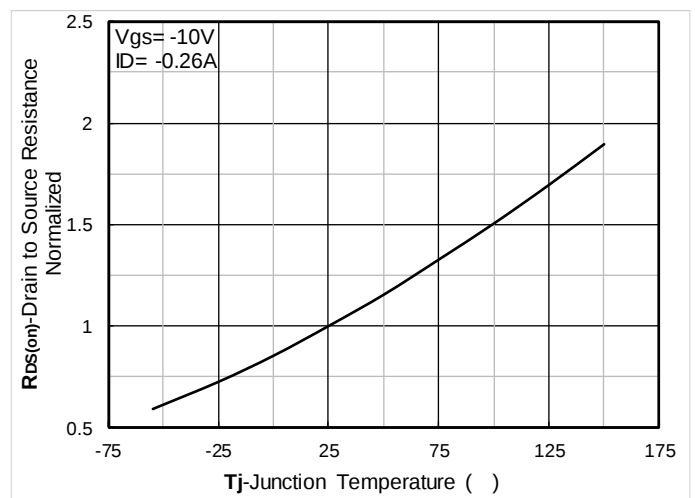


Figure 6. Normalized On-Resistance

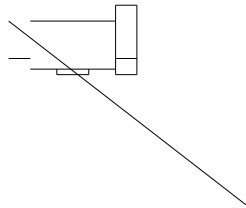
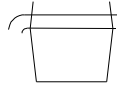
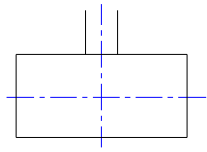


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area



SOT-523 Package information





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